



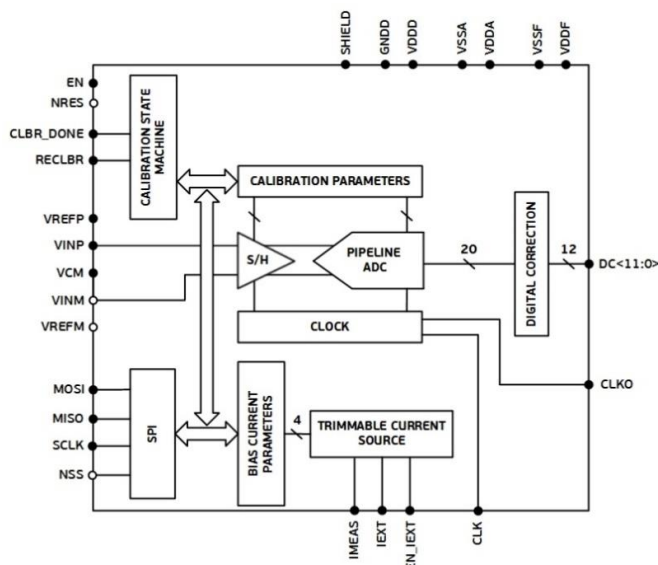
FEATURES

- 12-bit resolution
- Sample rate: 20 MSPS
- INL: ± 3 LSB
- DNL: ± 0.8 LSB
- ENOB at 1.3 MHz input: 10.1 bits

HIGHLIGHTS

- Fully differential architecture
- Integrated/external biasing choice
- Trimming mode of internal biasing
- Built-in calibration state machine for offset and gain calibration
- Built-in SPI for parameters tuning including Speed-to-Power Consumption ratio trimming
- Output clock for output data processing
- Separate analog and digital power supplies (5 V and 1.8 V correspondingly)

FUNCTIONAL BLOCK DIAGRAM



APPLICATIONS

- Space applications
- Communications
- SDR receivers
- Test and instrumentation

GENERAL DESCRIPTION

The TI-12PI/20M is a 12-bit analog-to-digital converter (ADC) with pipelined architecture and serial peripheral interface (SPI), which achieves conversion rate up to 20 MSPS. It has differential analog inputs and parallel data output. The device includes internal Sample & Hold (S&H) circuit, eight 1.5-bit stages, and one 4-bit Flash AD converter. Internal automatic prestart calibration system allows to tune consequently offset and gain of each pipeline stage using built-in analog calibration arrays for each parameter. Consequent calibration approach results in high static and dynamic parameters of the whole pipeline ADC system. The calibration module can be activated by power-on or by user. The SPI allows user to configure the following ADC parameters: biasing current, calibration coefficients of each stage, number of calibration iterations, delay between offset and gain calibrations.

User can make speed adjustment of operational amplifiers and comparators by adjusting internal current source or by using external current source for biasing. To increase speed, current should also be increased, but power consumption in this case rises as well. Thus, speed-to-power consumption ratio trimming is available.

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DEVICE PARAMETERS

$V_{DDA} = 4.5$ to 5.5 V, $V_{DDD} = 1.62$ to 1.98 V, $V_{SSA} = G_{NDD} = 0$ V; $V_{REFP} = V_{DDA}$, $V_{REFM} = 0$, $V_{CM} = 0.5 \cdot V_{DDA}$, $F_{CLK} = 20$ MHz, internal I_{BIAS} with default value (8), calibrated with internal routing, $T = -40$ to 150°C , unless otherwise noted

Symbol	Parameter	Min	Typ	Max	Unit	Conditions and comments
Accuracy ^{A)}						
N	Resolution		12		Bits	
INL	Integral nonlinearity		±3.15	±3.31	LSB	F _{in} = 1.3 MHz sine wave; F _{CLK} = 20 MHz
DNL	Differential nonlinearity		±0.86	±1.06	LSB	
OE	Offset error		±0.68	±2.38	LSB	
GE	Gain error		0.99	1.00	%	
Dynamic parameters ^{A)}						
ENOB	Effective number of bits	9.26	9.93	10.10	Bits	F _{in} = 1.3 MHz sine wave; F _{CLK} = 20 MHz
SNR	Signal-to-Noise ratio	59.9	62.5	63.6	dB	
SINAD	Signal-to-Noise and distortion ratio	57.5	61.5	62.5	dB	
SFDR	Spurious-Free Dynamic Range	61.9	68.8	70.75	dB	
THD	Total Harmonic Distortion	0.3	0.4	0.8	m%	
Reference inputs						
VREFP	High reference voltage	VCM+2		VDDA	V	
VREFM	Low reference voltage	VSSA		VCM-2	V	
VCM	Common mode voltage	2	2.5	3	V	
C _{REFP}	VREFP input capacitance		15.4		pF	
C _{REFM}	VREFM input capacitance		17.7		pF	
C _{CM}	VCM input capacitance		3.6		pF	
I _{refp}	Current through VREFP ^{A)}	1.95	2.44	4.04	mA	Sourcing, dynamic
I _{refm}	Current through VREFM ^{A)}	1.95	2.44	4.04	mA	Sinking, dynamic
Analog inputs						
	Input voltage range	-(VREFP-VREFM)		VREFP+VREFM	V	(VINP-VINM)
C _{INA}	Input capacitance ^{B)}	800			fF	VINP (VINM)
R _{INA}	Input resistance ^{B)}	500			Ohm	
Digital inputs ^{C)}						
V _{IH}	Input high voltage level	1.4			V	
V _{IL}	Input low voltage level			0.4	V	
C _{EN}	Input capacitance of «EN»			96	fF	

DEVICE PARAMETERS (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Conditions and comments
C _{EN_IEXT}	Input capacitance of «EN_IEXT»			76	fF	
C _{CLK}	Input capacitance of «CLK»			832	fF	
C _{NRES}	Input capacitance of «NRES»	7			pF	
C _{MOSI}	Input capacitance of «MOSI»	136			fF	
C _{NSS}	Input capacitance of «NSS»	148			fF	
C _{SCLK}	Input capacitance of «SCLK»	355			fF	
C _{RECLBR}	Input capacitance of «RECLBR»	178			fF	
Digital outputs						
V _{OH}	Output high voltage level			V _{DDD}	V	
V _{OL}	Output low voltage level	0			V	
C _L	Load capacitance ^{C)}	500			fF	Rising/falling edge is 2 ns
Current consumption ^{A)}						
I _{dda}	Analog part	27.4	33.8	44.2	mA	F _{CLK} = 20 MHz
I _{ddd}	Digital part	1.2	3.8	4.3	mA	
I _{ddf}	Clock module	3.8	4.4	4.9	mA	
Timing ^{C)}						
F _{CLK}	Clock frequency			20	MHz	
t _A	Aperture delay	2.8	3.7	6.1	ns	
t _{CLK-CLKO}	CLK-CLKO delay		4.9		ns	
t _L	Pipeline latency		7		periods	
SPI timing						
F _{SCLK}	SPI clock frequency			20	MHz	
t _{SU}	Setup time of data after a rising edge of SPI clock	25			ns	
t _{HD}	Hold time of data after a falling edge of SPI clock	25			ns	
t _L	Leading time before the first SPI clock edge	50			ns	
t _T	Trailing time after the last SPI clock edge	50			ns	
t _I	Idling time between transfers	50			ns	

Notes:

^{A)} Parameter is derived from measurements performed on 30 sampled devices from single wafer

^{B)} Input resistance and input capacitance represent on-resistance of input switch and total capacitance of the Hold capacitor

^{C)} Simulation results, 3-sigma statistical calculation

PIN FUNCTIONAL DESCRIPTION

Pin name	Description	Comments
EN	Enable ADC	Active level - high
VREFP	High reference voltage	
VINP	Analog input (+)	
VCM	Common-mode voltage	
VINM	Analog input (-)	
VREFM	Low reference voltage	
EN_IEXT	Enable external current source	Active level – high, disables internal biasing
CLK	Clock input	
NRES	Reset	Active level - low
MISO	Master input slave output	
MOSI	Master output slave input	
NSS	Slave select	Active level – low
SCLK	SPI input clock	
DC<11:0>	Digital output data <11:0>	
CLKO	Clock output	
RECLBR	Recalibration	Activates at falling edge
CLBR_DONE	“End of calibration” output signal	Active level - high
IMEAS	Current measurement output	
IEXT	External current input	
VDDF	Clock module power supply	Typical value: 5 V
VSSF	Clock module ground	
VDDA	Analog power supply	Typical value: 5 V
VSSA	Analog ground	
VDDD	Digital power supply	Typical value: 1.8 V
GNDD	Digital ground	
SHIELD	Shield (ground)	

DEVICE OPERATION

This analog-to-digital converter has pipelined architecture with internal Sample and Hold circuit. The input equivalent circuit is given in Figure 1.

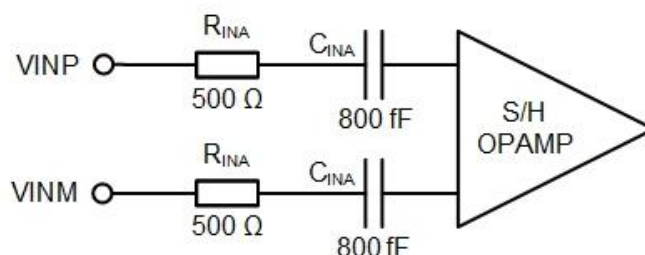


Figure 1. Equivalent analog input circuit (during sampling phase)

Input signal source output resistance must be also considered for proper sampling as shown in Figure 2.

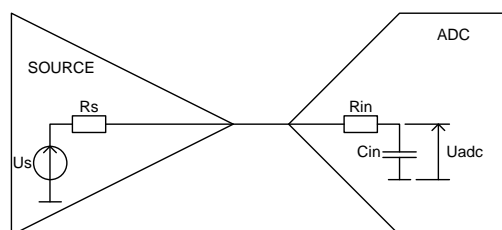


Figure 2. Equivalent electrical circuit of signal source and ADC

The time constant of the circuit, to achieve an error less than 1/16LSB, is given by:

$$TC_{1/16LSB} = (R_s + R_{IN}) \times C_{IN} \times \ln 2^{(N+4)}$$

Where N is the resolution of the converter (in this case N=12).

The required input time constant must be small enough to be within the given ADC analog input sampling time. The acquisition for $TC_{1/16LSB}$ should be used for calculation of maximum value of external driving source resistance to provide a desired ADC conversion accuracy.

The pipeline conversion core includes eight 1.5-bit stages and one 4-bit flash ADC. Every 1.5-bit stage receives an analog signal from the previous stage and produces output data that is sent further to the digital error-correction module.

S/H and every subsequent conversion stage have additional DACs for calibration of offset and gain of each stage. These DACs are controlled with stored register values. The process of data writing into the registers is performed by calibration state machine or by a user through SPI. In case of low «NSS» signal a user performs the process of data writing into all internal registers (not only calibration registers), otherwise the calibration is carried out automatically. During automatic calibration several iterations (256 iterations by default) with averaging are performed for the binary search of tuning coefficients. Approximate calibration time is calculated as follows:

$$t_{cal} \approx n_{iter} \times T_{CLK} \times n_{c/iter}$$

Where n_{iter} is the number of iterations and $n_{c/iter}$ is the number of clock cycles per iteration.

At typical settings, the approximate time of calibration is 12.8 ms (~1000 clock cycles per iteration at 50 ns clock period). If recalibration is needed (for instance due to change in temperature), it can

be started by a pulse to «RECLBR». All the data of internal registers can be turned into default values via asserting «NRES» low.

Output data is valid for reading during falling edge of «CLKO». Latency of ADC is 7 input clock frequency periods. Sampling of the input signal is performed at the rising edge of «CLK» signal + aperture delay t_A (at the end of the sampling phase and the beginning of the hold phase).

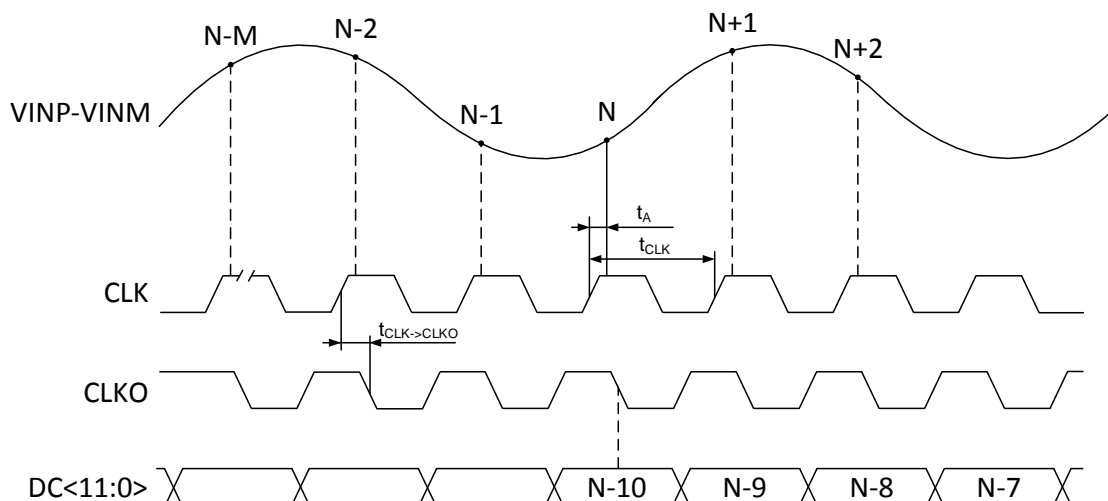


Figure 3. Timing diagram

Input signal charges the hold capacitor in Sample-and-Hold circuit during sample phase (when «CLK» is low) and S/H holds the value of the input signal at the end of the sample phase (at the rising edge of «CLK» + t_A).

Output data type is fully parallel.

The integrated SPI allows user to configure the ADC: biasing current, calibration coefficients of each stage, number of calibration iterations, delay between offset and gain calibrations.

The ADC's SPI operates as a slave relative to a user.

For reading or writing operation 16 bits should be transmitted to «MOSI». The first 8 bits is address (MSB defines reading if it is low and writing if it is high), and following 8 bits is data. The data in the SPI is latched at the falling edge of «SCLK». The transmitted data format is «LSB - first». Therefore, the reading/writing bit is the 8th bit in this chain.

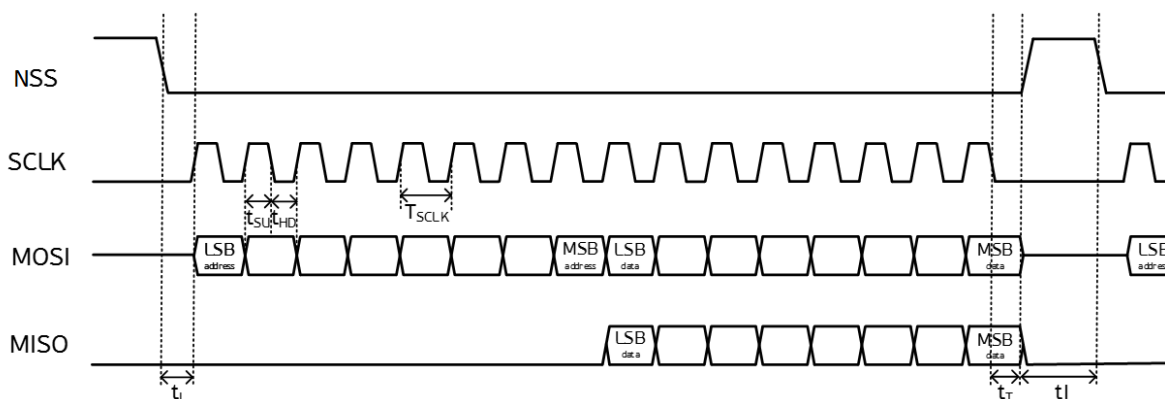


Figure 4. SPI timing diagram

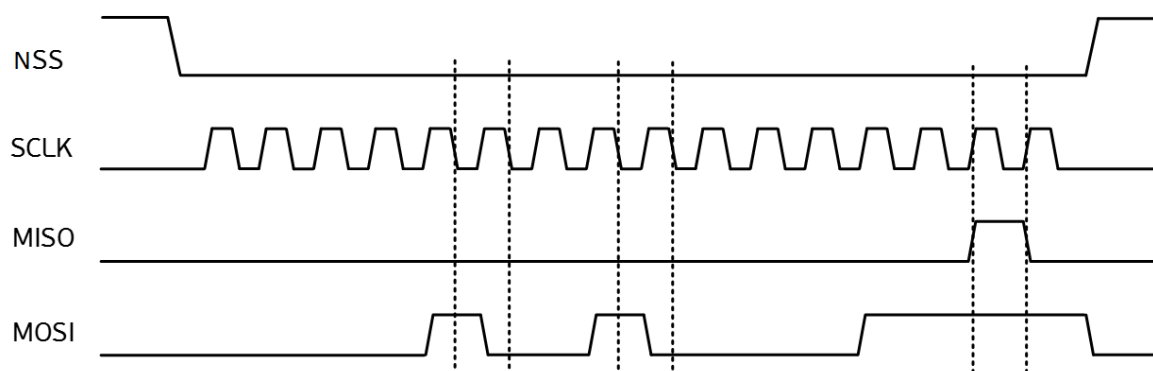


Figure 5. SPI example

On figure 5 there is an example of writing the data F0 into a gain tuning coefficient for the S/H register (0x90). Simultaneously default data of the register is being transmitted from the ADC to «MISO».

MEMORY MAP REGISTERS TABLE

Address	B7	B6	B5	B4	B3	B2	B1	B0	Description
0x00	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 1st stage (reading); default value: 40
0x80	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 1st stage (writing)
0x01	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 1st stage (reading); default value: 0
0x81	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 1st stage (writing)
0x02	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 2nd stage (reading); default value: 40
0x82	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 2nd stage (writing)
0x03	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 2nd stage (reading); default value: 0
0x83	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 2nd stage (writing)
0x04	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 3rd stage (reading); default value: 40
0x84	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 3rd stage (writing)
0x05	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 3rd stage (reading); default value: 0
0x85	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 3rd stage (writing)
0x06	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 4th stage (reading); default value: 40
0x86	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 4th stage (writing)
0x07	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 4th stage (reading); default value: 0
0x87	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 4th stage (writing)
0x08	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 5th stage (reading); default value: 40
0x88	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 5th stage (writing)
0x09	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 5th stage (reading); default value: 0
0x89	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 5th stage (writing)
0x0A	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 6th stage (reading); default value: 40
0x8A	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 6th stage (writing)
0x0B	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 6th stage (reading); default value: 0
0x8B	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 6th stage (writing)

MEMORY MAP REGISTERS TABLE (continued)

0x0C	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 7th stage (reading); default value: 40
0x8C	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 7th stage (writing)
0x0D	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 7th stage (reading); default value: 0
0x8D	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 7th stage (writing)
0x0E	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 8th stage (reading); default value: 40
0x8E	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for 8th stage (writing)
0x0F	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 8th stage (reading); default value: 0
0x8F	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for 8th stage (writing)
0x10	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for S/H (reading); default value: 40
0x90	-	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Gain tuning coefficient for S/H (writing)
0x11	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for S/H (reading); default value: 0
0x91	Sign	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Offset tuning coefficient for S/H (writing)
0x28	-	-	-	-	3 rd bit	2 nd bit	1 st bit	0 th bit	Internal current source settings (reading); default value: 8
0xA8	-	-	-	-	3 rd bit	2 nd bit	1 st bit	0 th bit	Internal current source settings (writing)
0x20	7 th bit	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Number of calibration iterations settings (reading); default value: 2F
0xA0	7 th bit	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Number of calibration iterations settings (writing)
0x22	7 th bit	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Settings for delay between calibration states (reading); default value: 2
0xA2	7 th bit	6 th bit	5 th bit	4 th bit	3 rd bit	2 nd bit	1 st bit	0 th bit	Settings for delay between calibration states (writing)

INTERNAL CURRENT SOURCE

The implemented current source is a general purpose current source. It is supplied from VDDA source for operation and has one output that drives typical current of 60 μA at typical combination "1000" for trimming inputs B<3:0>.

Internal current source output current (VDDA = 5 V, T = 27°C)

Code	Output current, μA
B<3:0>=0000	20.0
B<3:0>=0001	25.0
B<3:0>=0010	30.0
B<3:0>=0011	35.0
B<3:0>=0100	39.9
B<3:0>=0101	44.9
B<3:0>=0110	49.9
B<3:0>=0111	54.8
B<3:0>=1000	59.7
B<3:0>=1001	64.7
B<3:0>=1010	69.6
B<3:0>=1011	74.5
B<3:0>=1100	79.4
B<3:0>=1101	84.3
B<3:0>=1110	89.2
B<3:0>=1111	94.1

External current for biasing must be in the same range as internal current source output, that is from 20 μA to 94 μA .

REQUIREMENTS FOR POWER SUPPLY AND GROUND NETS

Analog and digital power supplies wiring should be split, because the analog blocks require isolation from digital power supply noise.

REQUIREMENTS FOR EXTERNAL COMPONENTS

Analog inputs need a differential input buffer that should meet the requirements to analog inputs: analog inputs capacitance and sample rate.

Input buffer SNR should be more than 80 dB at desired input frequency (for example, 3 MHz).

Reference inputs also require buffers meeting the requirements to reference inputs according to the Device Parameters table.

Analog input buffer should be placed as close as possible to the analog inputs. The length of analog inputs paths («VINP»/«VINM») should be equal.

The reference input buffers are necessary. They should be placed as close as possible to the reference inputs («VREFP», «VCM», «VREFM»).

It is recommended to use 10 uF tantalum (or 100 uF low ESR electrolytic) capacitor in parallel with 100 nF ceramic capacitor as external capacitors for supply and ground nets. Keep the PCB tracks as short as possible to ground and to capacitors.

CRITICAL APPLICATION NOTES

«VREFP», «VCM», «VREFM», «VINP» and «VINM» are highly sensitive analog signals: any noise at these inputs or cross-talks from high frequency signals to these pins can alter overall ADC accuracy. Thus, it is recommended to shield these signals with analog ground, and fast-switching signals should never be run near (under/over) metal lines leading to these input pins.

Although «VDDF» and «VDDA» are of the same voltage, their wiring should be split, because «VDDF» is a supply for clock buffers and it is considered rather noisy.

It is recommended to connect «SHIELD» with «VSSA».

TYPICAL PERFORMANCE CHARACTERISTICS

The figures are obtained by measurements. Due to the inevitable lot-to-lot tolerances, the values given below may differ from typical values in the table above.

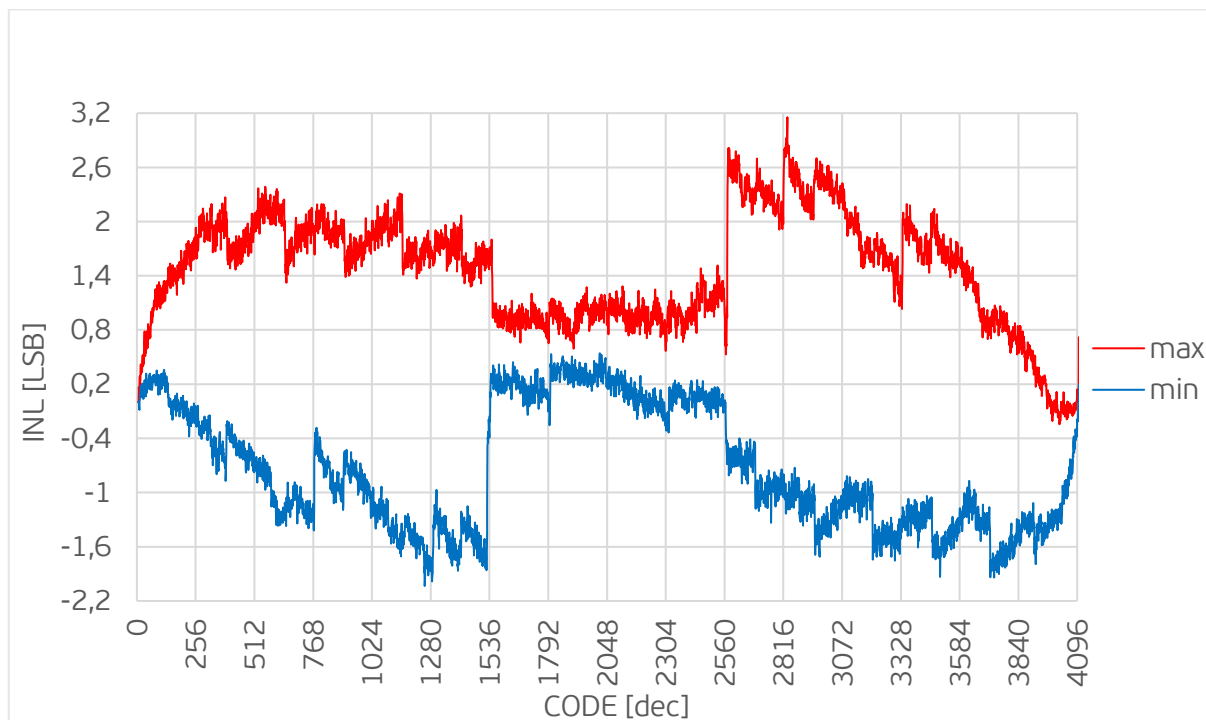


Figure 6. Minimal and maximal INL vs output code at typical conditions
($V_{DDA} = V_{REFP} = 5\text{ V}$; $V_{DDD} = 1.8\text{ V}$; $T = 27^{\circ}\text{C}$; $F_{CLK} = 20\text{ MHz}$; $F_{in} = 1.3\text{ MHz}$)



Figure 7. Minimal and maximal DNL vs output code at typical conditions
($V_{DDA} = V_{REFP} = 5\text{ V}$; $V_{DDD} = 1.8\text{ V}$; $T = 27^{\circ}\text{C}$; $F_{CLK} = 20\text{ MHz}$; $F_{in} = 1.3\text{ MHz}$)

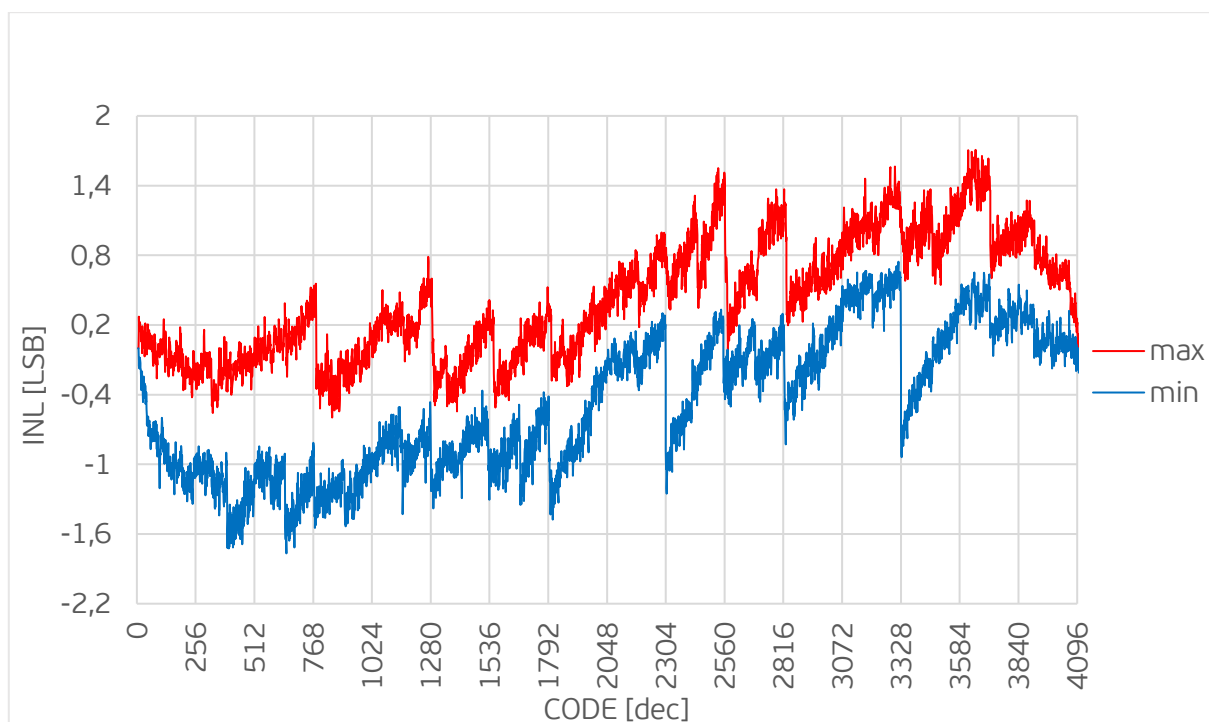


Figure 8. Minimal and maximal INL vs output code at high temperatures
($V_{DDA} = V_{REFP} = 4.5\text{ V}$; $V_{DDD} = 1.62\text{ V}$; $T = 150^{\circ}\text{C}$; $F_{CLK} = 20\text{ MHz}$; $F_{in} = 1.3\text{ MHz}$)

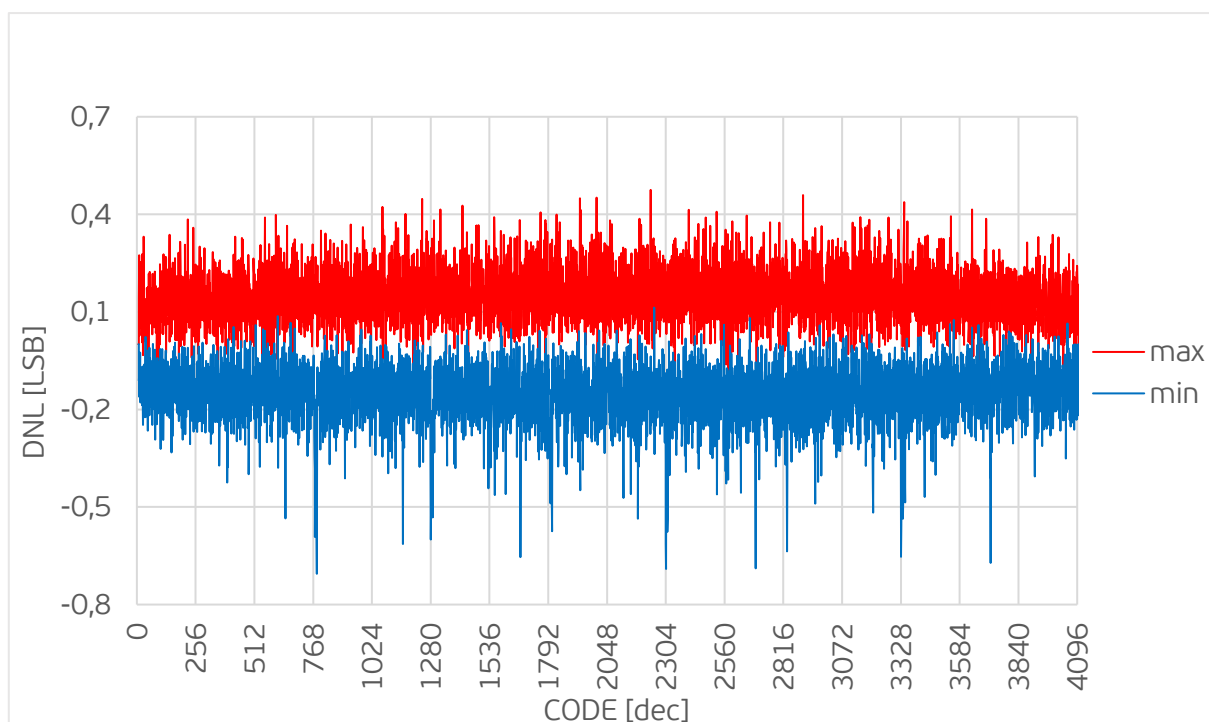


Figure 9. Minimal and maximal DNL vs output code at high temperatures
($V_{DDA} = V_{REFP} = 4.5\text{ V}$; $V_{DDD} = 1.62\text{ V}$; $T = 150^{\circ}\text{C}$; $F_{CLK} = 20\text{ MHz}$; $F_{in} = 1.3\text{ MHz}$)

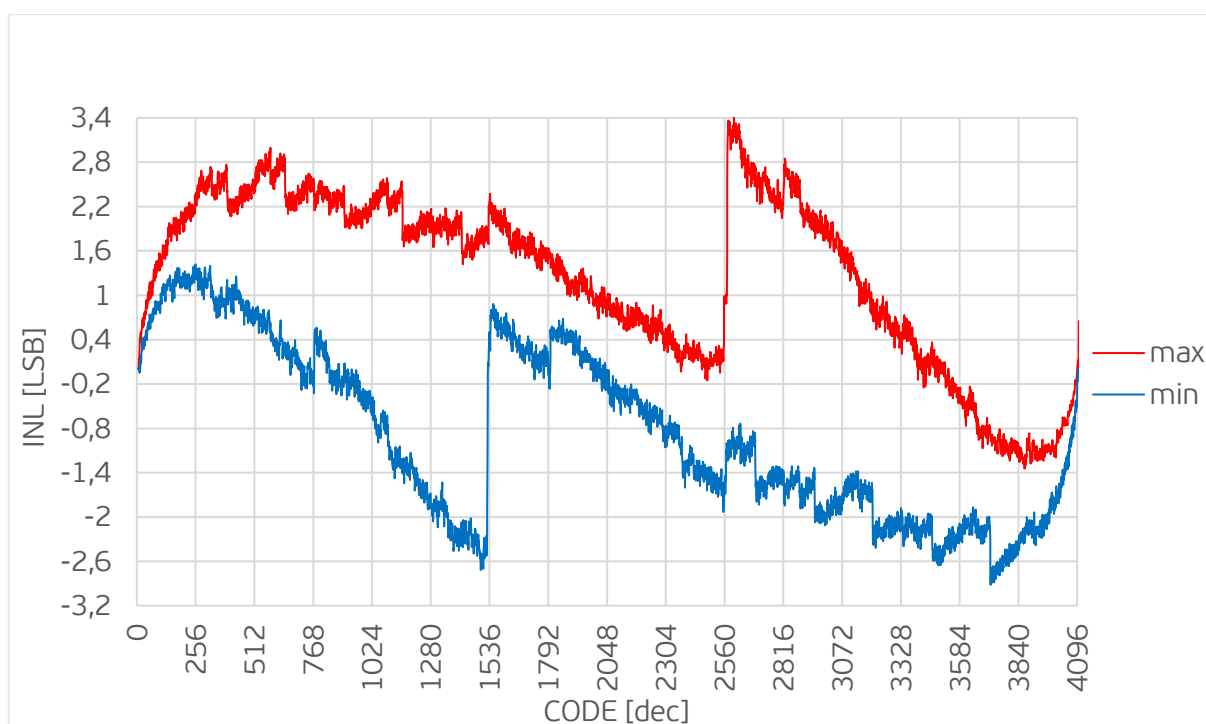


Figure 10. Minimal and maximal INL vs output code at low temperatures
($V_{DDA} = V_{REFP} = 5.5\text{ V}$; $V_{DDD} = 1.98\text{ V}$; $T = -40^{\circ}\text{C}$; $F_{CLK} = 20\text{ MHz}$; $F_{in} = 1.3\text{ MHz}$)

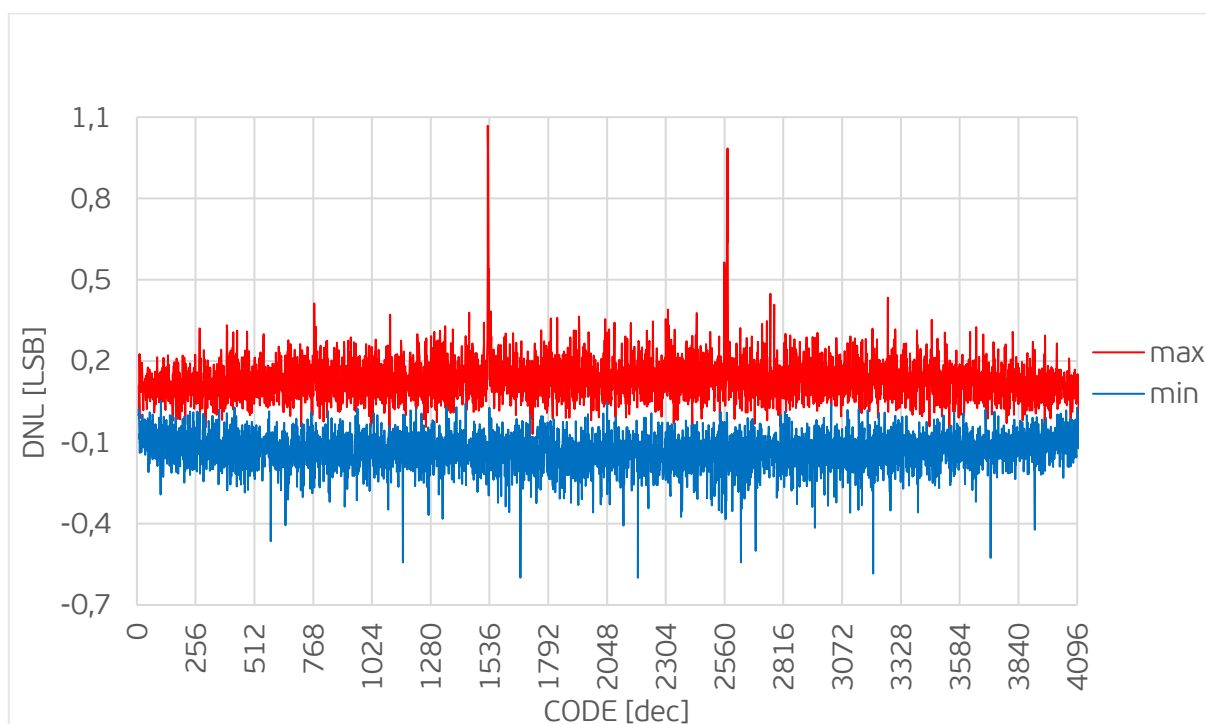


Figure 11. Minimal and maximal DNL vs output code at low temperatures
($V_{DDA} = V_{REFP} = 5.5\text{ V}$; $V_{DDD} = 1.98\text{ V}$; $T = -40^{\circ}\text{C}$; $F_{CLK} = 20\text{ MHz}$; $F_{in} = 1.3\text{ MHz}$)